		(2400)	ATTY DOCKET A	CEDIAL NO					
FORM PTO-1449 (MODIFIED)					ATTY DOCKET N	SERIAL NO.			
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)					67,200-377 Filed Herewith				with
					APPLICANT Fu-Liang Yang				
					FILING DATE Filed Herewith	GRO	GROUP Unknown		
REFERENCE DI	SIGNAT	ION U.S. I	PATENT DOCUM	IENT	S				
EXAMINER INITIAL		DOCUMĖNT NO.	DATE		NAME	C	LASS	SUB CLASS	FILING DATE
DP	AA	5,023,671	Jun/1991	Di	Vincenzo et al			_	
DF	AB	5,119,151	Jun/1992	Or	nda				
	AC`								
	AD								
	ΑE								
	AF								
	AG								
	АН								
	Al								
	AJ								
			FOREIGN	PAT	ENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NO.	DATE		COUNTRY	CLA		SUB CLASS	TRANSLATION YES/NO
	A K								
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	AM	,				_			
	AN_			<u>.</u>					
		OTHER A	RT (including A	uthor	, Title, Date, pertinent	pages,	etc.)		
DP	AO	Sallagoity et al, "Analysis of Width Edge Effects in Advanced Isolation Schemes for Deep Submicron CMOS Technologies", IEEE Trans. on Electron Devices, 44(11), Nov. 1996, pp. 1900-05.							
OF	АР	Matsuda et al, "Novel Corner Rounding Process for Shallow Trench Isolation Utilizing MSTS (Micro-Structure Transformation of silicon). IEEE IEDM98, pp. 137-40.							

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

EXAMINER